

IN THE CLAIMS:

A complete listing of all the claims is now presented.

Claims 1 - 12. (Cancelled).

Claim 13. (Currently Amended).

A semiconductor wafer, comprising  
a substrate wafer made of monocrystalline silicon and an  
epitaxial layer deposited thereon;

said substrate wafer having a resistivity of from 0.1 to  
50  $\Omega\text{cm}$ , an oxygen concentration of less than  $7.5 \times 10^{17} \text{ atcm}^{-3}$  and a  
nitrogen concentration of from  $1 \times 10^{13}$  to  $5 \times 10^{15} \text{ atcm}^{-3}$ ; and

the epitaxial layer has a thickness of from 0.2 to 1.0  $\mu\text{m}$   
and has a top surface on which fewer than 30 LLS defects with a  
size of more than 0.085  $\mu\text{m}$  can be detected.

Claim 14. (Previously Presented).

The semiconductor wafer as claimed in claim 13,  
wherein the oxygen concentration of the substrate wafer is  
less than  $6.5 \times 10^{17} \text{ atcm}^{-3}$ .

Claim 15. (Previously Presented) .

The semiconductor wafer as claimed in claim 13,  
wherein the nitrogen concentration of the substrate wafer

lies in a range of from  $1 \times 10^{14}$  to  $5 \times 10^{14}$   $\text{atcm}^{-3}$ .

Claims 16 to 24 (Cancelled).

Claim 25. (Currently Amended).

A semiconductor wafer consisting of  
a substrate wafer made of monocrystalline silicon and an  
epitaxial layer deposited thereon;  
said substrate wafer having a resistivity of from 0.1 to 50  
 $\Omega\text{cm}$ , an oxygen concentration of less than  $7.5 \times 10^{17}$   $\text{atcm}^{-3}$  and a  
nitrogen concentration of from  $1 \times 10^{13}$  to  $5 \times 10^{15}$   $\text{atcm}^{-3}$ ; and  
the epitaxial layer has a thickness of from 0.2 to 1.0  $\mu\text{m}$   
and has a top surface on which fewer than 30 LLS defects with a  
size of more than 0.085  $\mu\text{m}$  can be detected.

Claim 26. (Previously Presented).

The semiconductor wafer as claimed in claim 25,  
wherein the oxygen concentration of the substrate wafer is  
less than  $6.5 \times 10^{17}$   $\text{atcm}^{-3}$ .

Claim 27. (Previously Presented).

The semiconductor wafer as claimed in claim 25,  
wherein the nitrogen concentration of the substrate wafer  
lies in a range of from  $1 \times 10^{14}$  to  $5 \times 10^{14}$   $\text{atcm}^{-3}$ .